

09/806224 #5

JCS REC'D PCT/PTO 27 MAR 2001

Pre Amended
Revised
8/28/01

BEFORE THE UNITED STATES ELECTED OFFICE

In Re Application of: Grutzediek and Scheerer

Corresponding to International Application No.: PCT/EP99/05942

Filed: 13 August 1999

Title: Method for Producing Transistors

Box PCT
Assistant Commissioner for Patents
Washington, D.C. 20231

Attn: DO/EO/US

PRELIMINARY AMENDMENT

Dear Sir:

For the U.S. national phase, kindly rewrite pending claims 4, 7, 15, 22, 25, and 26 as follows:

4. (Amended) The method of Claim 2, wherein an n-doped junction area having heavier doping than that of the trough is produced in the n-doped fringe area of the trough and a p-doped area having heavier doping than that of the p-doped area enclosed by the p-doped inner area is produced in the p-doped area enclosed by the p-doped inner area.

7. (Amended) The method of Claim 5, wherein in the n-doped fringe area of the trough an n-doped area having heavier doping than that of the trough and in the n-doped area forming the base an n-doped area having heavier doping than that of the n-doped area forming the base and in the p-doped inner area a p-doped area having heavier doping than that of the p-doped inner area are produced.

15. (Amended) The method of Claim 13, wherein an n-doped area having heavier doping than that of the n-doped area forming the gate is inserted into the n-doped area forming the gate.